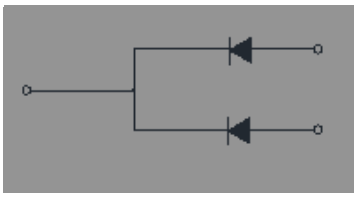
RoHS
COMPLIANT

- Adopt FRED chip
- Low forward Voltage drop
- Fast reverse recovery time
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.



002 and JESD22-B102

- : As marked

■ (Tj=25 Unless otherwise specified

Device marking code			MURB1060CT

Surge(Non-repetitive)Forward Current u	Tstg C	J	M -55 ~ +175

Junction Temperature	Tj		-55 ~ +175
Typical Junction capacitance @4V,1MHz	Cj	pF	20

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Instantaneous forward voltage drop per diode	V_{FM}	V	I_{FM}=5.0A @Tj=25		-	1.45	1.6
			I_{FM}=5.0A @Tj=150			1.15	1.3
DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	uA	V_{RM}=V_{RRM} Tj=25		-	-	5.0
	I_{RRM2}		V_{RM}=V_{RRM} Tj=150		-	35	200
Reverse Recovery Time	Trr	ns	I_F=0.5A I_{RM}=1A I_{RR}=0.25A Tj=25		-	25	35
			Tj=25	IF=5A di/dt=-200A/us V_{RM}=200V	-	50.8	-
			Tj=125		-	81.8	-
Peak recovery current	I_{RRM}	A	Tj=25		-	3.06	-
			Tj=125		-	5.07	-
Reverse recovery charge	Qrr	nC	Tj=25		-	78.88	-
			Tj=125		-	280	-

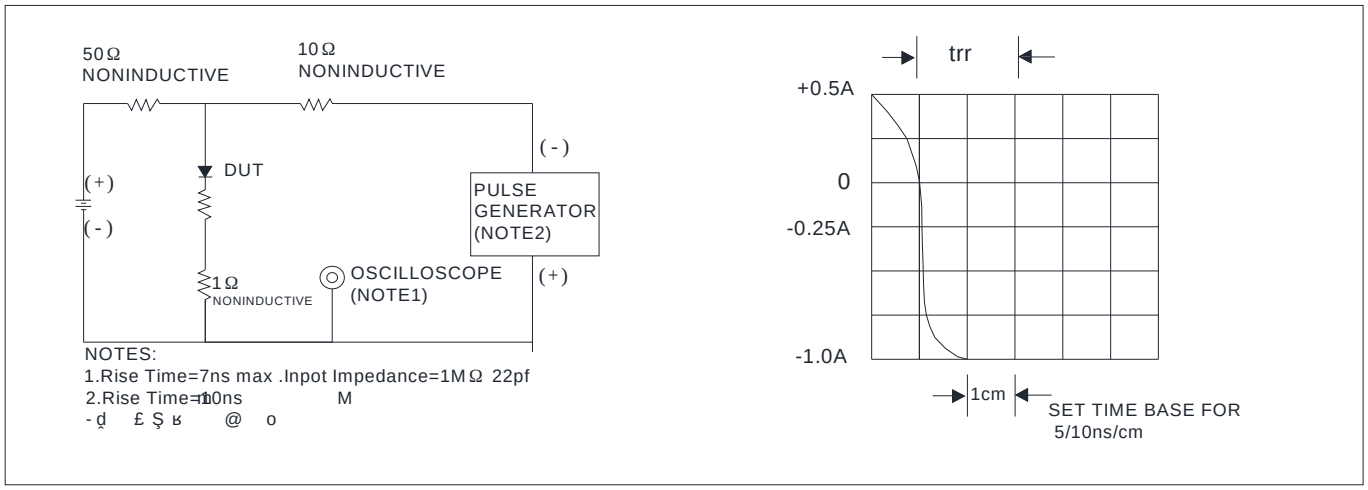
■ Tj=25 Unless otherwise specified

Thermal Resistance	Between junction and case	$R_{\theta J-C}$	/W	2.0
Thermal Resistance	Between junction and Air	$R_{\theta J-A}$	/W	50

■ (Example)

MURB1060CT	Approximate 1.43	50	2000	8000	Tube
MURB1060CT	Approximate 1.43	1000	2000	10000	Reel

■ (Typical)


50Ω
NONINDUCTIVE
10Ω
NONINDUCTIVE
DUT
(+)
(-)
PULSE
GENERATOR
(NOTE2)
(-)
(+)
1Ω
NONINDUCTIVE
OSCILLOSCOPE
(NOTE1)
NOTES:
1.Rise Time=7ns max .Inpot Impedance=1MΩ 22pf
trr
+0.5A
0
-0.25A
-1.0A
1cm
SET TIME BASE FOR
5/10ns/cm

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